Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π–MOSV)

2SK2841

Chopper Regulator, DC-DC Converter and Motor Drive Applications

• Low drain-source ON resistance : RDS (ON) = 0.4Ω (typ.) • High forward transfer admittance : $|Y_{fs}| = 8.0 S$ (typ.) • Low leakage current : $I_{DSS} = 100 \mu A$ (max) ($V_{DS} = 400 V$)

Enhancement mode : $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics Symbol Rating Unit Drain-source voltage V_{DSS} 400 ٧ Drain-gate voltage (R_{GS} = 20 k Ω) 400 V_{DGR} ٧ Gate-source voltage V_{GSS} ±30 DC (Note 1) 10 Α I_D Drain current Pulse (Note 1) 40 Α I_{DP} Drain power dissipation (Tc = 25°C) P_D W Single pulse avalanche energy 360 mJ EAS (Note 2) Avalanche current 10 I_{AR} Α Repetitive avalanche energy (Note 3) EAR 8 mJ °C Channel temperature 150 T_{ch} Storage temperature range -55~150 T_{stg}

10.3MAX. 63.6±0.2

10.3MAX. 63.6±0.2

1.6MAX. 0.76

1. GATE
2. DRAIN (HEAT SINK)
3. SOURCE

JEDEC TO-220AB

JEITA SC-46

TOSHIBA 2-10P1B

Weight: 2.0 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.56	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 5.85 mH, R_{G} = 25 Ω , I_{AR} = 10 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.



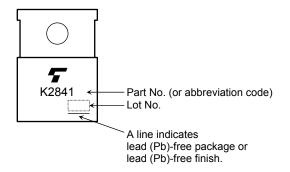
Electrical Characteristics (Ta = 25°C)

Charac	eteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V	_	_	±10	μΑ
Gate-source bre	eakdown voltage	V (BR) GSS	I _G = ±10 μA, V _{DS} = 0 V	±30	_	_	V
Drain cut-off cur	rrent	I _{DSS}	V _{DS} = 400 V, V _{GS} = 0 V	_	_	100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	400	_	_	V
Gate threshold v	oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source Ol	N resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 5.0 A	_	0.4	0.55	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 5.0 A	4.0	8.0	_	S
Input capacitano	е	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		1340	_	pF
Reverse transfer	r capacitance	C _{rss}			160	_	
Output capacitance		Coss			490	_	
Switching time	Rise time	t _r	$V_{GS} \stackrel{10V}{_{0V}} \stackrel{I_{D}=5.0A}{_{0V}} \stackrel{V_{OUT}}{_{R_{L}}} = 40\Omega$	_	22	_	- ns
	Turn-on time	t _{on}		_	60	_	
	Fall time	t _f		1	32		
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\mathbf{W}} = 10 \mu \text{s}$	1	140		
				34			
		Q _{gs}	$V_{DD} \approx 320 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$	_	18		nC
		Q _{gd}			16	_	

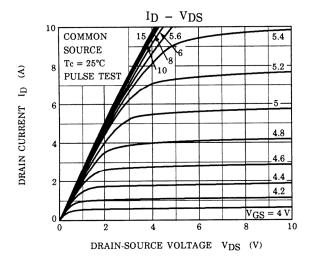
Source-Drain Ratings and Characteristics (Ta = 25°C)

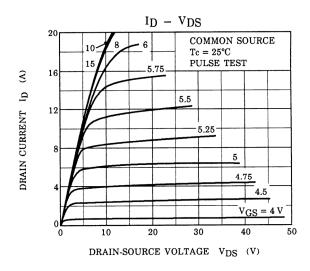
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	10	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	40	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 10 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 10 A, V _{GS} = 0 V		350	_	ns
Reverse recovery charge	Q _{rr}	dl _{DR} / dt = 100 A / μs	_	2.6	_	μC

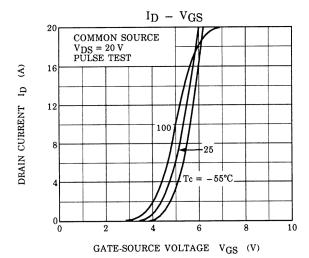
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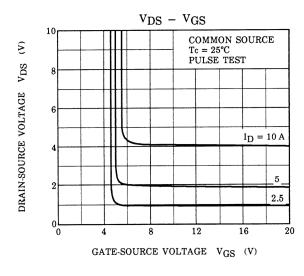


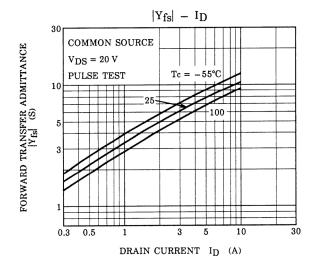
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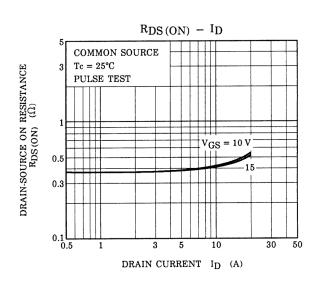




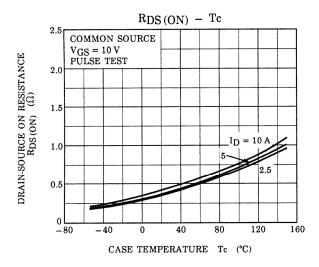


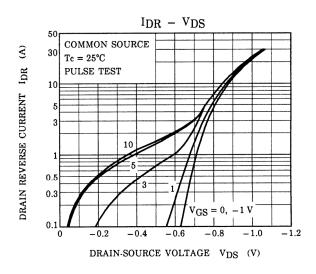


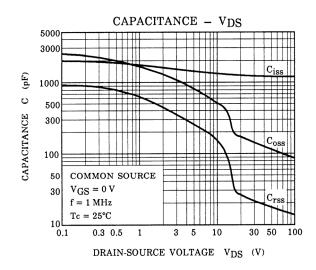


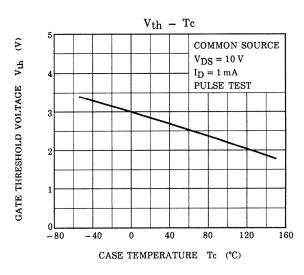


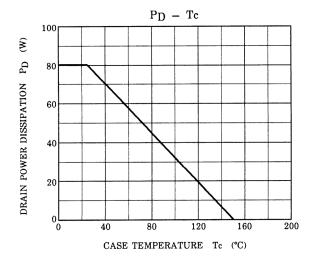
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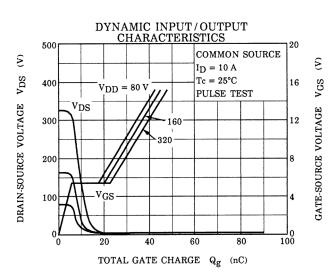


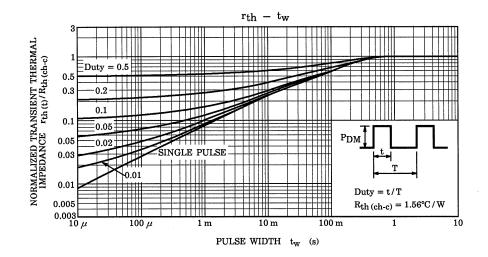


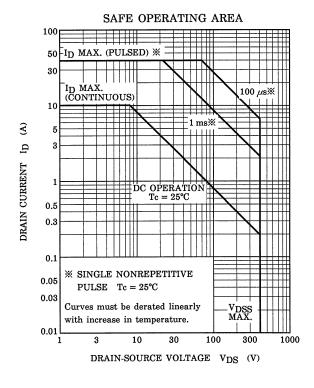


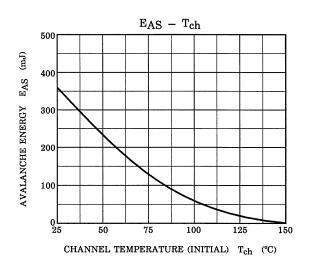


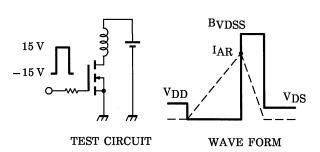












$$\begin{split} R_G &= 25~\Omega \\ V_{DD} &= 90~V,~L = 5.85~mH \end{split}$$

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$$E_{AS} = \frac{1}{2} \cdot L \cdot I^{2} \cdot \left(\frac{BVDSS}{BVDSS - VDD} \right)$$

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20070701-EN

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